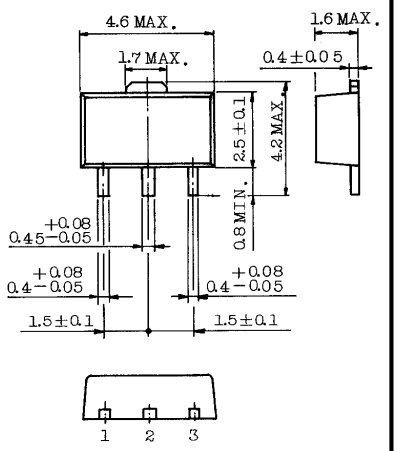
TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

2SC3607

VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

Unit in mm

- Low Noise Figure, High Gain.
- NF = 1.1dB, $|S_{21e}|^2$ = 9.5dB (f = 1GHz)



JEDEC	—
EIAJ	—
TOSHIBA	2-5K1A

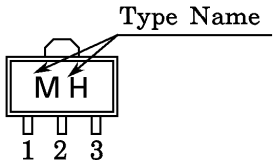
Weight : 0.05g

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	20	V
Collector-Emitter Voltage	V_{CEO}	12	V
Emitter-Base Voltage	V_{EBO}	3	V
Base Current	I_B	40	mA
Collector Current	I_C	80	mA
Collector Power Dissipation	P_C	400	mW
		(*) 800	
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	−55~125	°C

(*) When mounted ceramic substrate of 250mm² × 0.8t

Marking



MICROWAVE CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Transition Frequency	f_T	V_{CE} = 10V, I_C = 20mA	5	6.5	—	GHz
Insertion Gain	$\|S_{21e}\|^2$ (1)	V_{CE} = 10V, I_C = 20mA, f = 500MHz	—	15	—	dB
	$\|S_{21e}\|^2$ (2)	V_{CE} = 10V, I_C = 20mA, f = 1GHz	6	9.5	—	
Noise Figure	NF (1)	V_{CE} = 10V, I_C = 5mA, f = 1GHz	—	1.1	—	dB
	NF (2)	V_{CE} = 10V, I_C = 40mA, f = 1GHz	—	1.8	3	

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB} = 10V, I_E = 0	—	—	1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB} = 1V, I_C = 0	—	—	1	μA
DC Current Gain	h_{FE}	V_{CE} = 10V, I_C = 20mA	30	—	250	—
Collecter Output Capacitance	C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz (Note)	—	1.15	—	pF
Reverse Transfer Capacitance	C_{re}		—	0.8	1.25	pF

(Note) C_{re} is measured by 3 terminal method with Capacitance Bridge.

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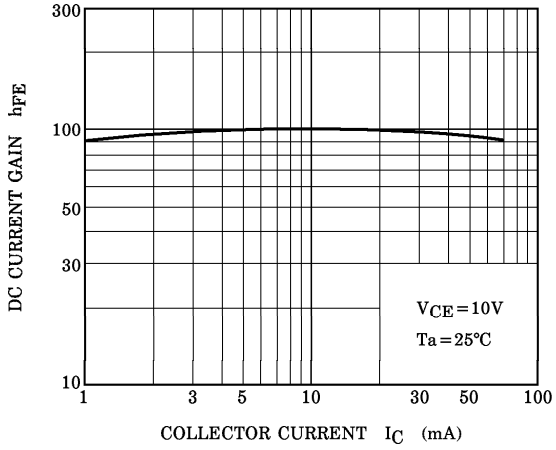
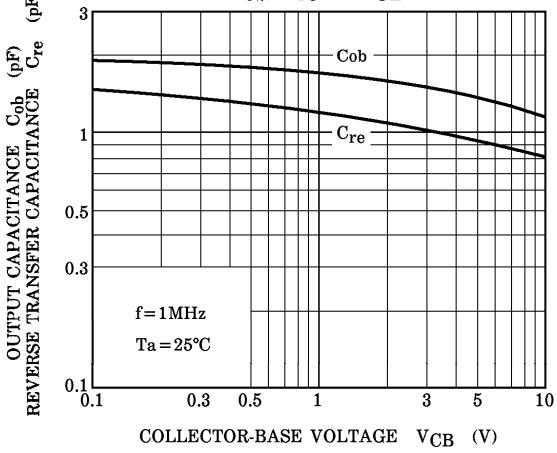
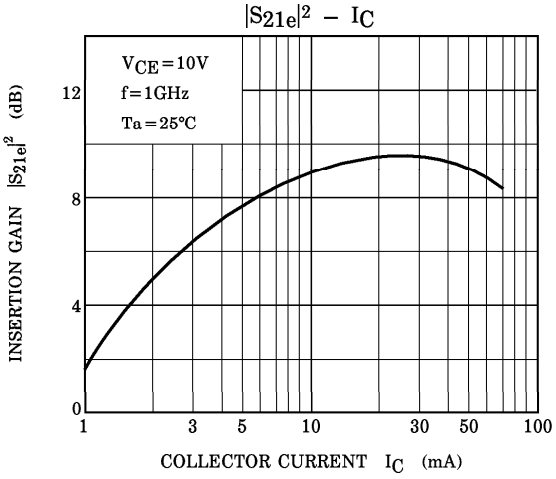
h_{FE} – I_C



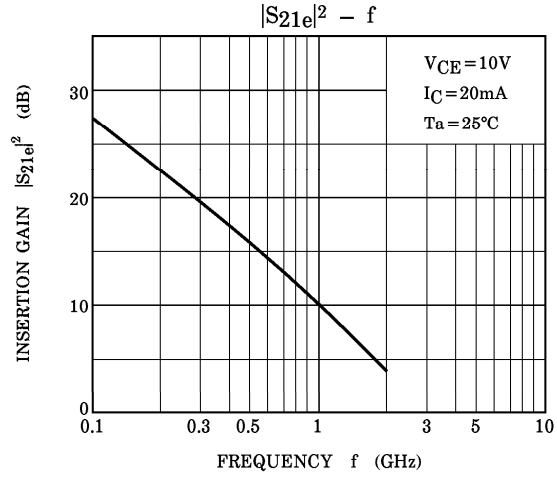
C_{ob}, C_{re} – V_{CB}



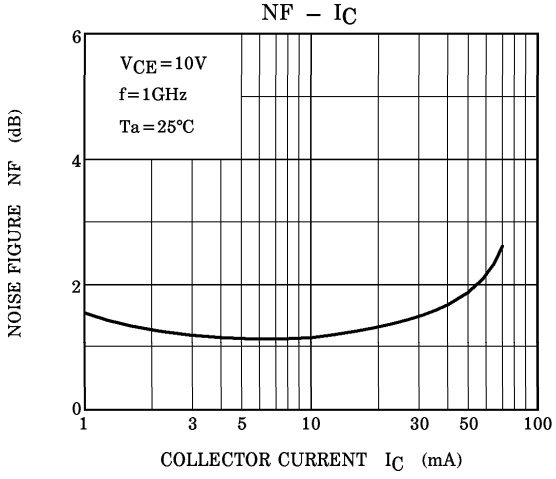
$|S_{21e}|^2$ – I_C



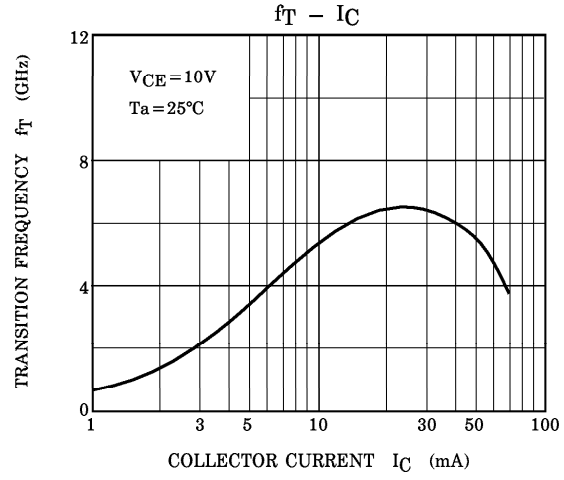
$|S_{21e}|^2$ – f



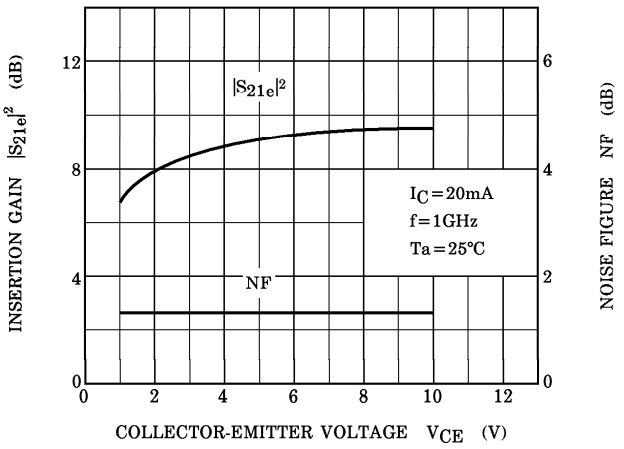
NF – I_C



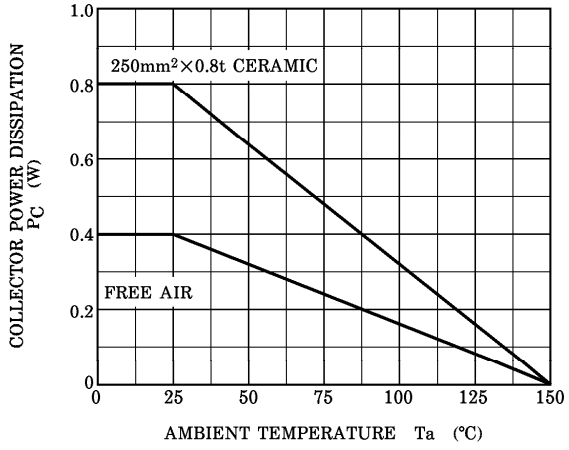
f_T – I_C



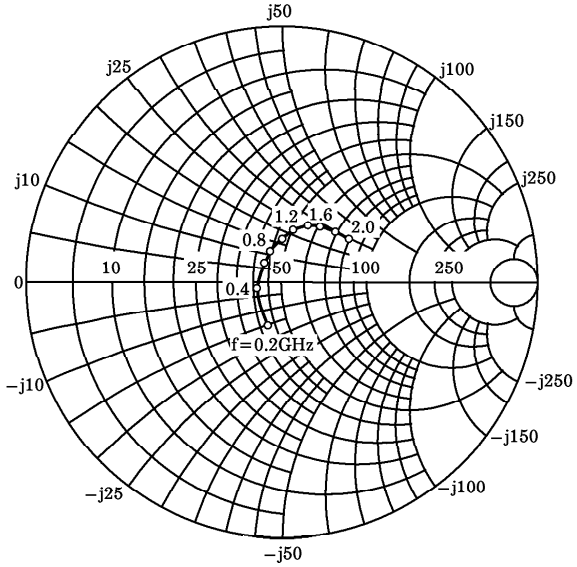
NF, $|S_{21e}|^2$ – V_{CE}



P_C – Ta



S_{11e}
V_{CE} = 10V
I_C = 20mA
Ta = 25°C
(UNIT : Ω)



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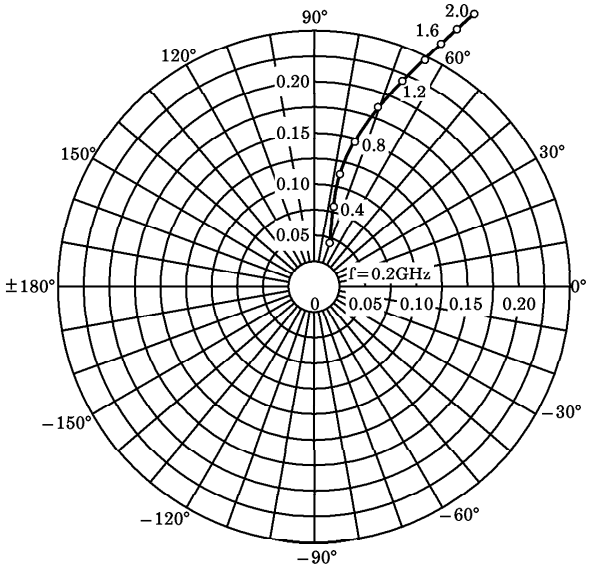

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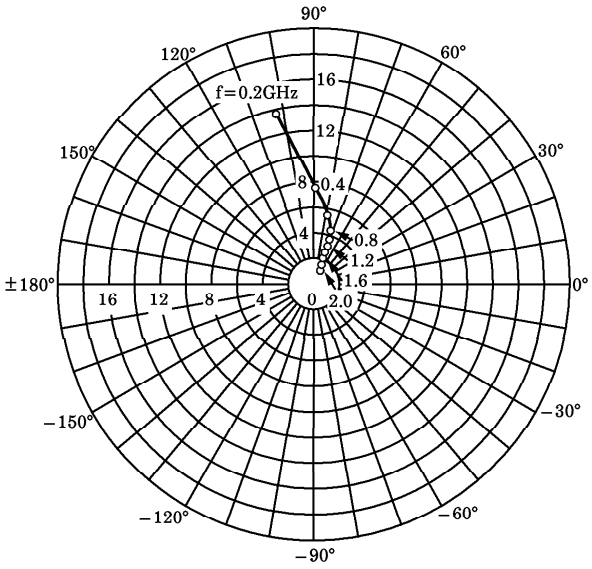

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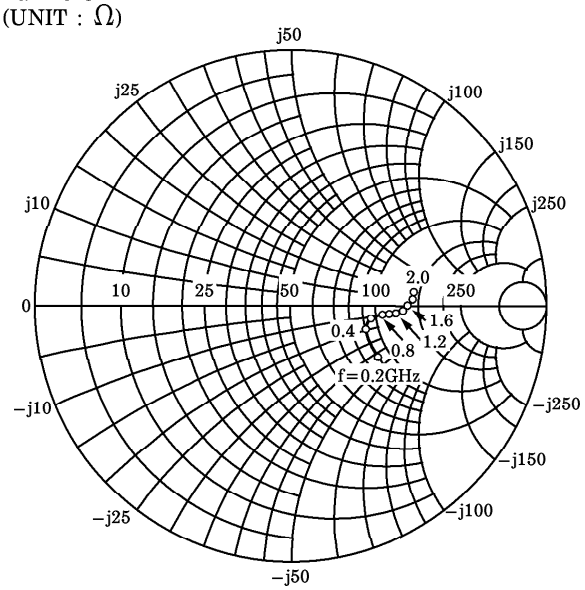

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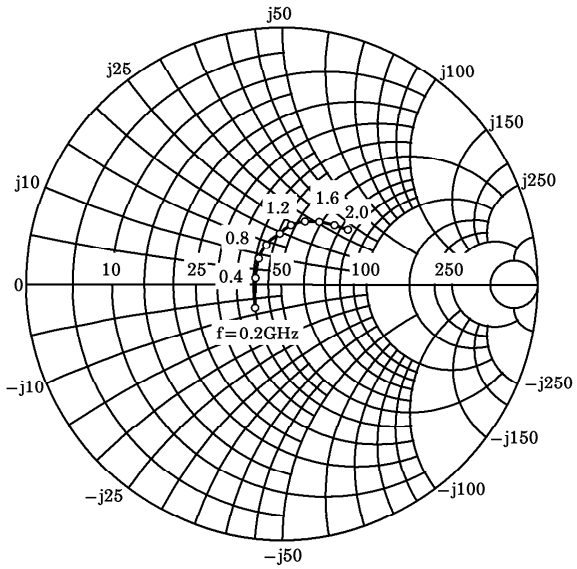

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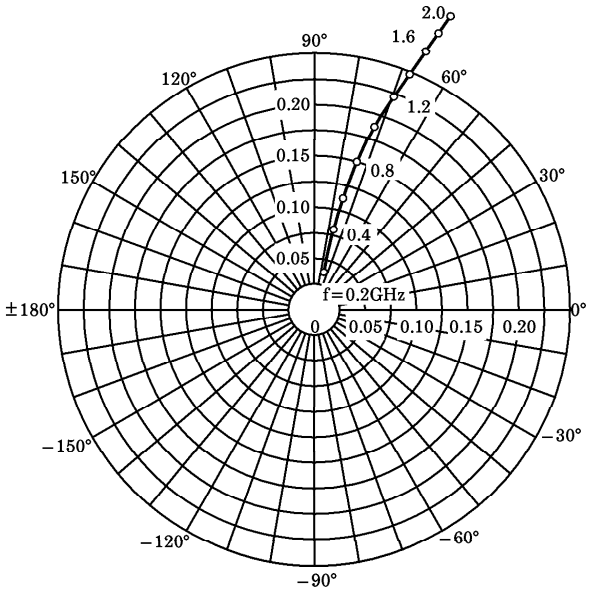

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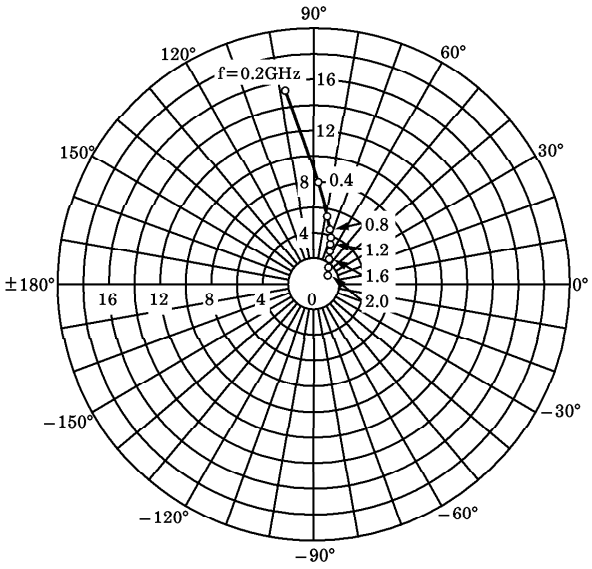

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